

HIGH-SPEED 32/16K x 18 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM

709379 ***709369**

*SPECIFIED PART IS OBSOLETE NOT RECOMMENDED FOR NEW DESIGNS

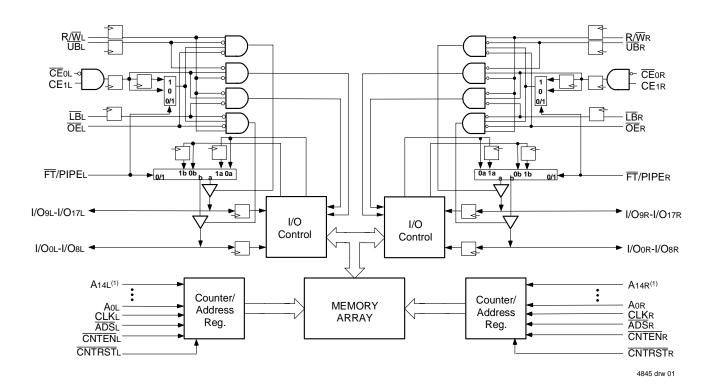
Features

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 7.5/9/12ns (max.)
 - Insustrial: 9ns (max.)
- Low-power operation
 - IDT709379/69L
 Active: 1.2W (typ.)
 Standby: 2.5mW (typ.)
- Flow-Through or Pipelined output mode on either Port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- Full synchronous operation on both ports
 - 4ns setup to clock and 0ns hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 7.5ns clock to data out in the Pipelined output mode
 - Self-timed write allows fast cycle time
 - 10ns cycle time, 100MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- ◆ TTL- compatible, single 5V (±10%) power supply
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 100-pin Thin Quad Flatpack (TQFP) package
- Green parts available, see ordering information

Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

Functional Block Diagram



NOTE:

1. A_{14x} is a NC for IDT709369.

FEBRUARY 2018



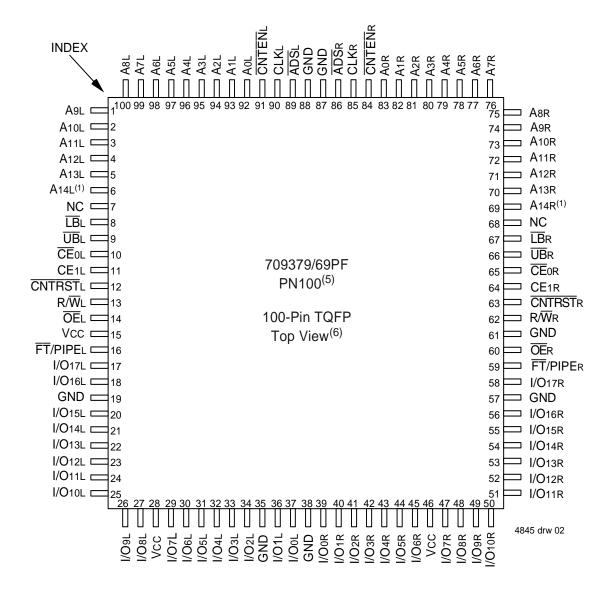
709379/69L High-Speed 32/16K x 18 Synchronous Pipelined Dual-Port Static RAM

Description

The IDT709379/69 is a high-speed 32/16K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times.

With an input data register, the IDT709379/69 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE} 0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using CMOS high-performance technology, these devices typically operate on only 1.2W of power.

Pin Configurations (1,2,3)



- 1. A14x is a NC for IDT709369.
- 2. All Vcc pins must be connected to power supply
- 3. All GND pins must be connected to ground.
- 4. Package body is approximately 14mm x 14mm x 1.4mm
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.



Pin Names

Left Port	Right Port	Names
CE _{0L} , CE _{1L}	CEOR, CE1R	Chip Enables ⁽³⁾
R/\overline{W}_L	R/\overline{W}_R	Read/Write Enable
ŌĒL	ŌĒR	Output Enable
A0L - A14L ⁽¹⁾	A0R - A14R ⁽¹⁾	Address
1/O0L - 1/O17L	I/O0R - I/O17R	Data Input/Output
CLKL	CLKR	Clock
ŪB∟	UB _R	Upper Byte Select ⁽²⁾
<u>LB</u> ∟	LB R	Lower Byte Selectt ⁽²⁾
ADSL	ADS R	Address Strobe
<u>CNTEN</u> ∟	<u>CNTEN</u> R	Counter Enable
CNTRST∟	CNTRST _R	Counter Reset
FT/PIPEL	FT/PIPER	Flow-Through/Pipeline
V	cc	Power
G	ND	Ground

NOTES:

- 1. A14x is a NC for IDT709369.
- 2. \overline{LB} and \overline{UB} are single buffered regardless of state of $\overline{FT}/PIPE$.
- 3. \overline{CE} o and CE1 are single buffered when $\overline{FT}/PIPE = V_{IL}$, $\overline{\text{CE}}\text{o}$ and CE1 are double buffered when $\overline{\text{FT}}/\text{PIPE} = \text{V}_{\text{IH}},$ i.e. the signals take two cycles to deselect.

4845 tbl 01

Truth Table I—Read/Write and Enable Control(1,2,3)

ŌĒ	CLK	ՇĒ ₀	CE ₁	ŪB	ĪΒ	R∕ W	Upper Byte I/O9-17	Lower Byte I/Oo-8	Mode
Х	1	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	1	Х	L	Х	Х	Х	High-Z	High-Z	Deselected—Power Down
Х	1	L	н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	1	L	Н	L	Н	L	DATAIN	High-Z	Write to Upper Byte Only
Х	1	L	Н	Н	L	L	High-Z	DATAIN	Write to Lower Byte Only
Х	1	L	Н	L	L	L	DATAIN	DATAIN	Write to Both Bytes
L	1	L	Н	L	Н	Н	DATAout	High-Z	Read Upper Byte Only
L	1	L	Н	Н	L	Н	High-Z	DATAout	Read Lower Byte Only
L	1	L	Н	L	L	Н	DATAout	DATAout	Read Both Bytes
Н	Х	L	Н	L	L	Х	High-Z	High-Z	Outputs Disabled

NOTES:

- 1. "H" = V_{IH}, "L" = V_{IL}, "X" = Don't Care. 2. <u>ADS</u>, <u>CNTEN</u>, <u>CNTRST</u> = X.
- 3. $\overline{\text{OE}}$ is an asynchronous input signal.

4845 tbl 02



709379/69L

Industrial and Commercial Temperature Range

Truth Table II—Address Counter Control^(1,2,6)

110111	. 00.0		0.0.0					
External Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	Х	An	1	L ⁽⁴⁾	Х	н	Dvo (n)	External Address Used
Х	An	An + 1	1	Н	L ⁽⁵⁾	н	Dvo(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	1	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	A 0	1	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0

NOTES:

4845 tbl 03

- 1. "H" = VIH, "L" = VIL, "X" = Don't Care.
- 2. \overline{CE}_0 , \overline{LB} , \overline{UB} , and \overline{OE} = VIL; CE1 and R/ \overline{W} = VIH.
- 3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.
- 4. \overline{ADS} is independent of all other signals including \overline{CE}_0 , \overline{CE}_1 , \overline{UB} and $\overline{\overline{LB}}$.
- 5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CE₀, CE₁, UB and LB.
- 6. While an external address is being loaded (ADS = VIL), R/W = VIH is recommended to ensure data is not written arbitrarily.

Recommended Operating Temperature and Supply Voltage

Grade	Ambient Temperature ⁽²⁾	GND	Vcc
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

4845 tbl 04

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	٧
GND	Ground	0	0	0	٧
VIH	Input High Voltage	2.2		6.0 ⁽¹⁾	V
VIL	Input Low Voltage	-0.5 ⁽²⁾		0.8	V

4845 tbl 05

NOTES:

- 1. VTERM must not exceed Vcc + 10%.
- 2. $V_{IL} \ge -1.5V$ for pulse width less than 10ns.

Absolute Maximum Ratings(1)

Symbol	Rating	Commercial & Industrial	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-65 to +150	°C
TJN	Junction Temperature	+150	°C
Іоит	DC Output Current	50	mA

NOTES:

4845 tbl 06

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.
- 3. Ambient Temperature Under Bias. No AC Conditions. Chip Deselected.

Capacitance⁽¹⁾

 $(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	9	pF
Соит ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

4845 thi 07

- These parameters are determined by device characterization, but are not production tested.
- 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.
- 3. Cout also references Ci/o.

^{1.} This is the parameter TA. This is the "instant on" case temperature.



709379/69L
High-Speed 32/16K v. 18 Synchronous Pinelined Dual-Port Static RAM

Industrial and Commercial Temperature Range

DC Electrical Characteristics Over the Operating

Temperature Supply Voltage Range (Vcc = 5.0V ± 10%)

			70937		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
ILI	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $Vin = 0V$ to Vcc	ı	5	μΑ
llo	Output Leakage Current	$\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{CC}$	ı	5	μΑ
VoL	Output Low Voltage	IOL = +4mA	1	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4	_	V

4845 tbl 08

NOTE

1. At Vcc ≤ 2.0V input leakages are undefined.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $^{(3)}$ (Vcc = 5V \pm 10%)

101111	cratare and	Supply Voltage	riang	, -	(• 00	- 3 v .	- 10 /8)						
								9/69L7 Only	709379 Co & I	m'l	709379 Com'l		
Symbol	Parameter	Test Condition	Versi	on	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Typ. ⁽⁴⁾	Max.	Unit		
lcc	Dynamic Operating Current	CEL and CER= VIL	COM'L	L	250	440	250	400	230	355	mA		
	(Both Ports Active)	Outputs Disabled $f = fMAX^{(1)}$	IND	L	_	_	300	430	_				
ISB1	Standby Current	CEL = CER = VIH	COM'L	L	65	145	80	135	70	110	mA		
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	L	_	_	95	160	_	_			
ISB2	Standby Current	CE"A" = VIL and	COM'L	L	160	295	175	275	150	240	mA		
	(One Port - TTL Level Inputs)	CE"B" = VIH ⁽³⁾ Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L			175	295		_			
ISB3	Full Standby Current	Both Ports CER and	COM'L	L	0.2	5.0	0.5	3.0	0.5	3.0	mA		
	(Both Ports - CMOS Level Inputs)	CEL \geq Vcc - 0.2V VIN \geq Vcc - 0.2V or VIN \leq 0.2V, f = 0 ⁽²⁾	IND	L			0.5	6.0	_				
ISB4	Full Standby Current (One Port -	\overline{CE} "A" $\leq 0.2V$ and	COM'L	L	150	290	170	270	140	225	mA		
	CMOS Level Inputs)	CE"B" \geq Vcc - 0.2V ⁽⁵⁾ VIN \geq Vcc - 0.2V or VIN \leq 0.2V, Active Port Outputs Disabled, f = fMaX ⁽¹⁾	IND	L	_	_	190	290	_	_			

NOTES: 4845 tbl 09

- 1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 4. Vcc = 5V, $TA = 25^{\circ}C$ for Typ, and are not production tested. Icc Dc(f=0) = 150mA (Typ).
- 5. $CEx = VIL \text{ means } \overline{CE}_0x = VIL \text{ and } CE_1x = VIH$
 - $CEx = VIH means \overline{CE}_0x = VIH or CE_1x = VIL$
 - CEx \leq 0.2V means $\overline{\text{CE}}_{\text{0X}} \leq \underline{\text{0.2V}}$ and CE1x \geq Vcc 0.2V
 - $\overline{CEx} \ge Vcc 0.2V$ means $\overline{\overline{CE}}_{0x} \ge Vcc 0.2V$ or $\overline{CE}_{1x} \le 0.2V$
 - "X" represents "L" for left port or "R" for right port.



709379/69L
High-Speed 32/16K x 18 Synchronous Pinelined Dual-Port Static RAM Industrial and Commercial Temperature

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

4845 tbl 10

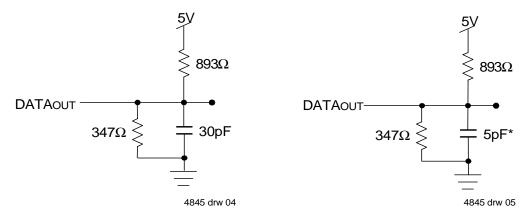


Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tckLz, tckHz, toLz, and toHz).
*Including scope and jig.

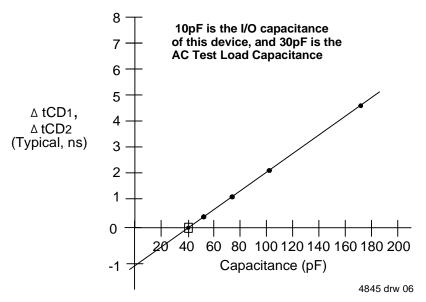


Figure 3. Typical Output Derating (Lumped Capacitive Load).



709379/69L
High-Speed 32/16K v. 18 Synchronous Pinelined Dual-Port Static RAM

Industrial and Commercial Temperature Rang

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{(3)}$ (Vcc = 5V ± 10%)

		709379/69L7 Com'l Only		709379/69L9 Com'l & Ind			9/69L12 I Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	22		25	_	30	_	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	12	_	15	_	20	_	ns
tcH1	Clock High Time (Flow-Through) ⁽²⁾	7.5	_	12	_	12	_	ns
tCL1	Clock Low Time (Flow-Through) ⁽²⁾	7.5	_	12	_	12	_	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	5		6		8		ns
tCL2	Clock Low Time (Pipelined) ⁽²⁾	5		6		8		ns
tr	Clock Rise Time		3		3		3	ns
tF	Clock Fall Time		3		3	_	3	ns
tsa	Address Setup Time	4		4		4		ns
tha	Address Hold Time	0	_	1		1	_	ns
tsc	Chip Enable Setup Time	4	_	4	_	4	_	ns
thc	Chip Enable Hold Time	0		1	_	1	_	ns
tsB	Byte Enable Setup Time	4	_	4	_	4	_	ns
tнв	Byte Enable Hold Time	0	_	1	_	1	_	ns
tsw	RW Setup Time	4		4	_	4	_	ns
tнw	RW Hold Time	0	_	1	_	1	_	ns
tsp	Input Data Setup Time	4		4	_	4	_	ns
thd	Input Data Hold Time	0		1	_	1	_	ns
tsad	ADS Setup Time	4		4		4	_	ns
thad	ADS Hold Time	0	_	1	_	1	_	ns
tscn	CNTEN Setup Time	4	_	4	_	4	_	ns
thon	CNTEN Hold Time	0	_	1	_	1	_	ns
tsrst	CNTRST Setup Time	4		4		4	_	ns
thrst	CNTRST Hold Time	0		1	_	1	_	ns
toE	Output Enable to Data Valid		7.5		9		12	ns
toLz	Output Enable to Output Low-Z ⁽¹⁾	2		2		2	_	ns
tonz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through)(2)	_	18		20	_	25	ns
tCD2	Clock to Data Valid (Pipelined)(2)	_	7.5		9	_	12	ns
tDC	Data Output Hold After Clock High	2		2	_	2	_	ns
tckhz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tcklz	Clock High to Output Low-Z ⁽¹⁾	2		2	_	2	_	ns
Port-to-Port D	Delay					•	•	
tcwdd	Write Port Clock High to Read Data Delay	_	28		35	_	40	ns
tccs	Clock-to-Clock Setup Time		10		15	_	15	ns

NOTES:

4845 tbl 11

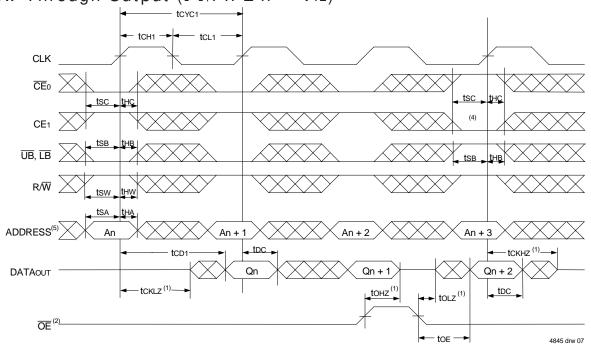
^{1.} Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

^{2.} The Pipelined output parameters (tcyc2, tcp2) to either the Left or Right ports when FT/PIPE = VIH. Flow-Through parameters (tcyc1, tcp1) apply when FT/PIPE = VIL for that port.

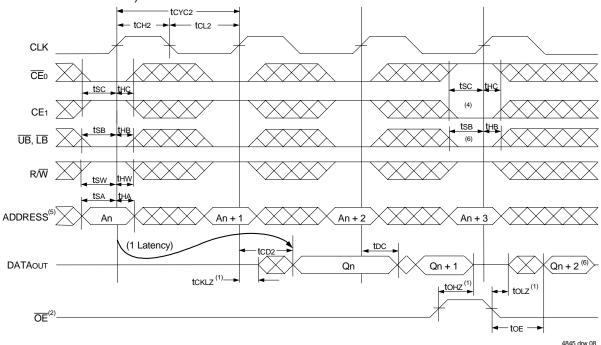
 $^{3. \}quad \text{All input signals are synchronous with respect to the clock except for the asynchronous Output Enable } (\overline{OE}), \ \overline{FT}/PIPER \ \text{and } \ \overline{FT}/PIPER \ \text{and } \ \overline{FT}/PIPER \ \text{on } \ \overline{FT}/PIPER$



Timing Waveform of Read Cycle for Flow-Through Output $(\overline{FT}/PIPE"x" = VIL)^{(3,7)}$

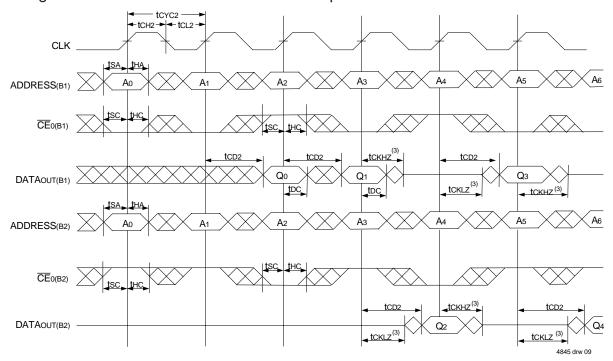


Timing Waveform of Read Cycle for Pipelined Operation $(\overline{FT}/PIPE"x" = VIH)^{(3,7)}$

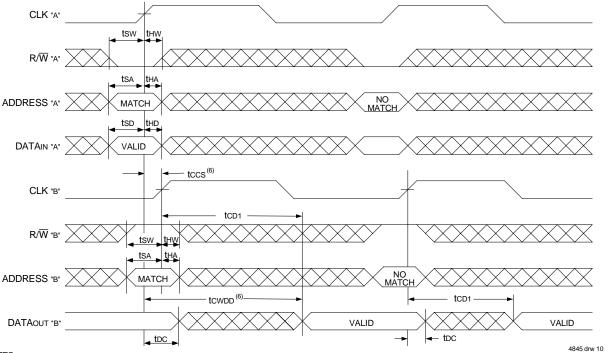


- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. \overline{OE} is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL \text{ and } \overline{CNTRST} = VIH.$
- 4. The output is disabled (High-Impedance state) by $\overline{\text{CE}}_0$ = V_{IH}, CE1 = V_IL, $\overline{\text{UB}}$ = V_IH, or $\overline{\text{LB}}$ = V_IH following the next rising edge of the clock. Refer to Truth Table 1.
- Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
 are for reference use only.
- 6. If $\overline{\text{UB}}$ or $\overline{\text{LB}}$ was HIGH, then the Upper Byte and/or Lower Byte of DATAOUT for Qn + 2 would be disabled (High-Impedance state).
- 7. "X" here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



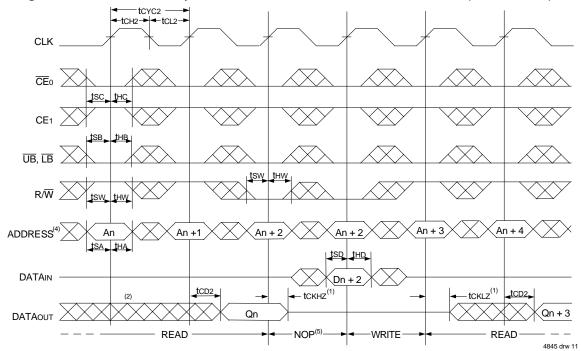
Timing Waveform of Write with Port-to-Port Flow-Through $Read^{(4,5,7)}$



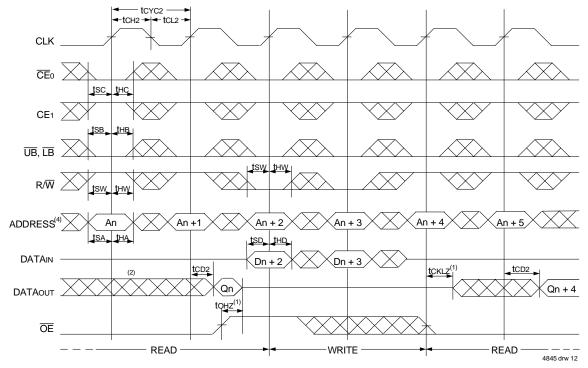
- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT709379/69 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/ \overline{W} and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_0 , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; CE1 and \overline{CNTRST} = \underline{VIH} .
- 5. $\overline{OE} = VIL$ for the Right Port, which is being read from. $\overline{OE} = VIH$ for the Left Port, which is being written to.
- If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwbb.
 If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb1. tcwbb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".



Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** = VIL)(3)



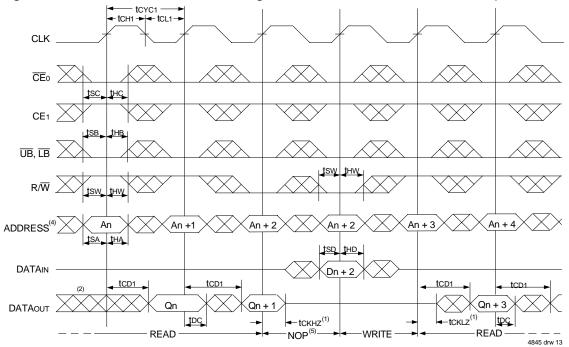
Timing Waveforn of Pipelined Read-to-Write-to-Read (OE Controlled)(3)



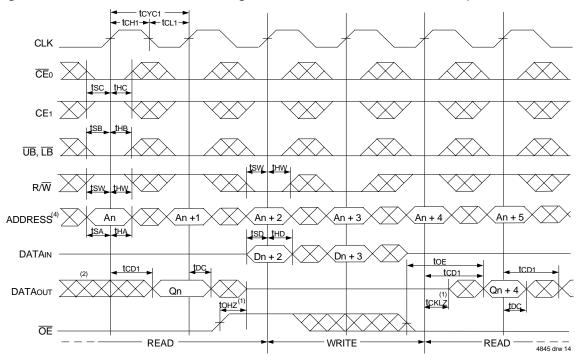
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$, $\overline{\text{UB}}$, $\overline{\text{LB}}$, and $\overline{\text{ADS}}$ = V_{IL}; CE₁ and $\overline{\text{CNTRST}}$ = V_{IH}. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.



Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{\textbf{OE}} = VIL$)⁽³⁾



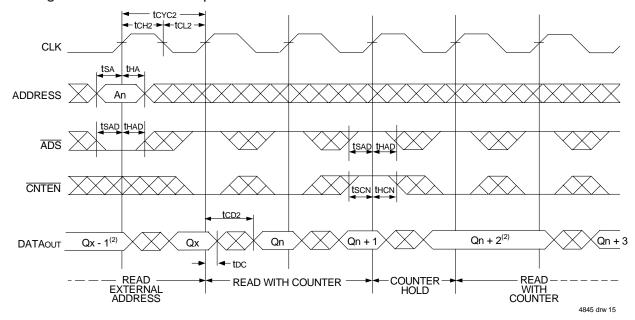
Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)(3)



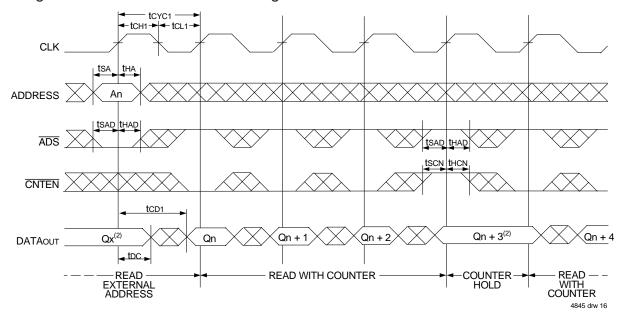
- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance is determined by the previous cycle control signals.
- 3. $\overline{\text{CE}}_0$, $\overline{\text{UB}}$, $\overline{\text{LB}}$, and $\overline{\text{ADS}}$ = V_{IL}; CE₁ and $\overline{\text{CNTRST}}$ = V_{IH}. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.



Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



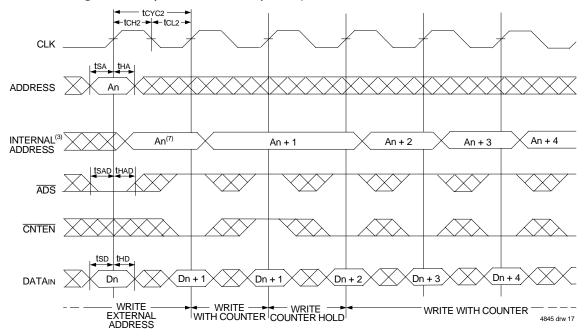
Timing Waveform of Flow-Through Read with Address Counter Advance (1)



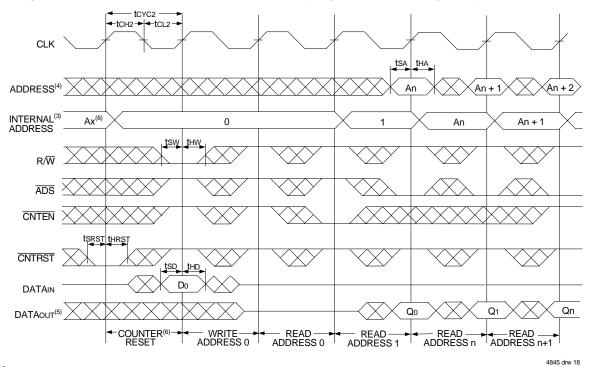
- 1. \overline{CE}_0 , \overline{OE} , \overline{UB} , and \overline{LB} = V_{IL}; CE₁, R/ \overline{W} , and \overline{CNTRST} = V_{IH}.
- 2. If there is no address change via $\overline{ADS} = VIL$ (loading a new address) or $\overline{CNTEN} = VIL$ (advancing the address), i.e. $\overline{ADS} = VIH$ and $\overline{CNTEN} = VIH$, then the data output remains constant for subsequent clocks.



Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)(1)



Timing Waveform of Counter Reset (Pipelined Outputs)(2)



- NOTES: 1. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and R/\overline{W} = VIL; $\overline{CE_1}$ and \overline{CNTRST} = VIH.
- \overline{CE}_0 , \overline{UB} , \overline{LB} = VIL; CE_1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = VIL$ and equals the counter output when $\overline{ADS} = VIH$.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle.
- CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.



709379/69L

A Functional Description

The IDT709379/69 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

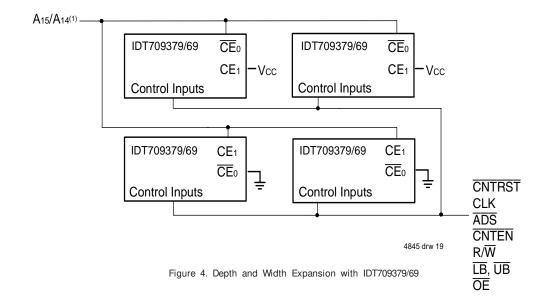
An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

 $\overline{\text{CE}}_0 = \text{VIH}$ or CE1 = VIL for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT709379/69's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{\text{CE}}_0 = \text{VIL}$ and CE1 = VIH to reactivate the outputs.

Depth and Width Expansion

The IDT709379/69 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT709379/69 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.

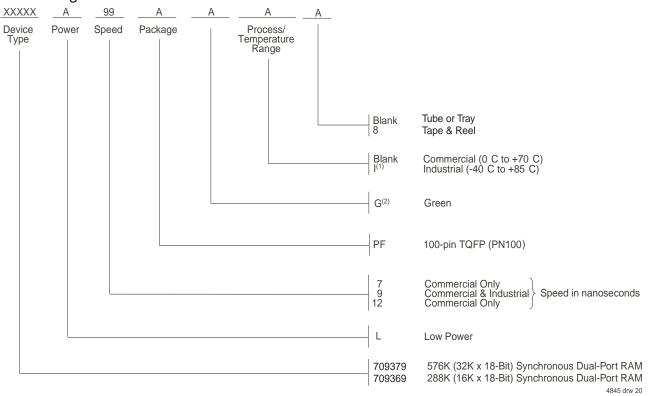


NOTE:

1. A₁₄ is for IDT709369.



Ordering Information



- 1. Industrial temperature range is available. For other speeds, packages and powers contact your sales office
- $2. \quad \text{Green parts available. For specific speeds, packages and powers contact your sales of fice.} \\$ LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02 $\underline{\text{Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience}.$



Datasheet Document History

9/30/99: Initial Public Release
11/10/99: Replaced IDT log
12/22/99: Page 1 Added nmissing diamond

12/22/99. Page I Added Illinssing diamond

1/12/01: Page 4 Changed information in Truth Table II

Increased storage temperature parameter

Clarified TA parameter

Page 5 DC Electrical parameters—changed wording from "open" to "disabled"

Changed ±200mV to 0mV in notes Removed Preliminary status

04/26/04: Consolidated multiple devices into one datasheet

Removed I-temp footnote

Page 2 Added date revision to pin configuration

Page 4 Added Junction Temperature to Absolute Maximum Ratings Table

Added Ambient Temperature footnote

Page 5 Added I-temp numbers for 9ns speed to the DC Electrical Characteristics Table

Added 6ns speed DC timing numbers to the DC Electrical Characteristics Table

Page 7 Added I-temp for 9ns speed to AC Electrical Characteristics Table

Added 6ns speed AC timing numbers to the AC Electrical Characteristics Table

Page 15 Added 6ns speed grade and 9ns I-temp to ordering information

Added IDT Clock Solution Table

Page 1 & 16 Replaced old ™ logo with new ™ logo
01/29/09: Page 15 Removed "IDT" from orderable part number
07/26/10: Page 1 Added green parts availability to features
Page 15 Added green indicator to ordering information

Page 7 In order to correct the header notes of the AC Elect Chars Table and align them with the Industrial temp range

values located in the table, the commercial TA header note has been removed

Pages 8-11 In order to correct the footnotes of timing diagrams, CNTEN has been removed to reconcile the footnotes with

the CNTEN logic definition found in Truth Table II - Address Counter Control

07/16/15: Page 1 Updated speed offerings by removing the 6.5ns commercial grade in Features

Page 2 Removed IDT in reference to fabrication

Page 2 & 15 The package code PN100-1 changed to PN100 to match standard package codes

Page 5 Removed X6 speed grade from the DC Elec Chars table
Page 6 Corrected typo in the Typical Output Derating drawing
Page 7 Removed X6 speed grade from the AC Elec Chars table

Page 16 Added Tape and Reel indicator to, removed X6 speed grade and updated the commercial offerings in

Ordering Information

Page 15 Removed the IDT Clock Solution table

02/08/18: Product Discontinuation Notice - PDN# SP-17-02

Last time buy expires June 15, 2018

04/24/19: 709369 is obsolete

709379 is still active

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